

Monday, September 28, 2026									
Start	End	Duration	Session	Number	Speaker	Organization	Country	Title	Chairs
08:45	09:00	00:15	Opening Remarks						
09:00	09:45	00:45	Keynote 1	KN1	Maud Vinet	Quobly	France	Building industrial-scale quantum computing on silicon	
09:45	10:15	00:30	S1 - Quantum	S1-INV1	Mathilde Lemang	Qphox	The Netherlands	Design and process development of integrated quantum transducers for scalable quantum systems	
10:15	10:35	00:20		S1-01	François Lefloch	CEA IRIG	France	Low temperature properties of CoSi ₂ based superconducting transistors	
10:35	10:55	00:20	Coffee Break						
10:55	11:15	00:20	S2 - Contact 1	S2 - 01	Shigehisa Shibayama	Nagoya University	Japan	Ultra-low Schottky barrier height in epitaxial-CaGe ₂ /n-Ge(111) contact: What is the key to lowering SBH of germanide/n-Ge contact?	
11:15	11:35	00:20		S2 - 02	Marie Merlin	CEA-Leti	France	Insights into Early Phase Formation in Ti-Based Contacts for Advanced FD-SOI	
11:35	11:55	00:20		S2 - 03	Jonas Müller	LAAS-CNRS	France	Engineering of nano-scale contacts for 3D silicon devices through geometrical confinement of binary and ternary nickel silicide alloys	
11:55	13:30	01:35	Lunch Break						
13:30	13:45	00:15	S3 - Special Session	S3 - 01	<i>tbd</i>	imec	Belgium	NanoC Pilot Line	
13:45	14:00	00:15		S3 - 02	Dominique Noguet	CEA-Leti	France	FAMES Pilot Line	
14:00	14:15	00:15	Short Break						
14:15	14:45	00:30	S4 - Annealing 1	S4 - INV1	Ray Duffy	Tyndall National Institute / University College Cork	Ireland	Doping solutions through recrystallisation of amorphous semiconductors; issues and challenges for planar CMOS, thin-body devices, and thin-film materials	
14:45	15:05	00:20		S4 - 01	Taiga Fuse	Institute of Science Tokyo	Japan	Edge-Contacted PVD-ZrS ₂ Field Effect Transistor with Reduced Thermal Budget by H ₂ S Annealing	
15:05	15:25	00:20		S4 - 02	Mahsa Shekarnoush	MicroSol Technologies Inc.	USA	High-Fractional Dopant Activation in Ultra-Shallow Junction Semiconductor Devices via Low-Temperature Plasma-Enhanced Annealing	
15:25	15:45	00:20		S4 - 03	Anthony Albanese	Sumitomo (SHI) Material Solutions Europe	France	Polycrystalline silicon grain size tuning and dopant activation by laser annealing	
15:45	16:05	00:20	Coffee Break						
16:05	16:35	00:30	S5 - Power devices	S5 - INV1	TaeGi Lee	Asahi Kasei Corp. / Nagoya University	Japan	MOVPE-Grown Pseudomorphic AlN/GaN/AlN HEMTs on AlN Substrates Enabling High Breakdown Field and Collapse-Free Operation	
16:35	17:05	00:30		S5 - INV2	Jan Prominski	Axcelis Technologies	Germany	Enabling SiC Superjunction Power Devices by Ultra-High-Energy Ion Implantation	
17:05	17:20	00:15	S6 - Poster Session Teasing	Each poster presenter is allotted two minutes for their introduction, which should be presented on a single slide					
17:20	18:00	00:40	S6 - Poster Session						
19:00	21:00	02:00	Conference Dinner						